GPN2222A NPN EPITAXIAL PLANAR TANSISTOR

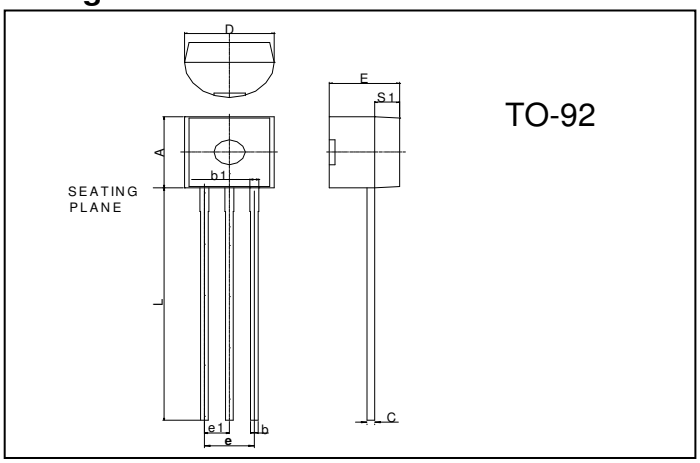
Description

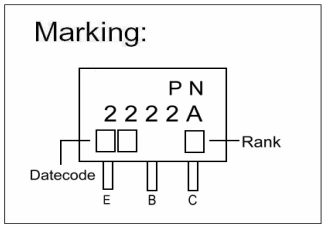
The GPN2222A is designed for general purpose amplifier and high speed, medium-power switching applications.

Features

*Low Collector Saturation Voltage
*High Speed Switching
*For Complementary Use with PNP Type GPN2907A

Package Dimensions





REF.	Millimeter		REF.	Millimeter	
	Min.	Max.		Min.	Max.
A	4.45	4.7	D	4.44	4.7
S_1	1.02	-	E	3.30	3.81
b	0.36	0.51	L	12.70	-
b_1	0.36	0.76	e1	1.150	1.390
C	0.36	0.51	e	2.42	2.66

Absolute Maximum Ratings at Ta = 25℃

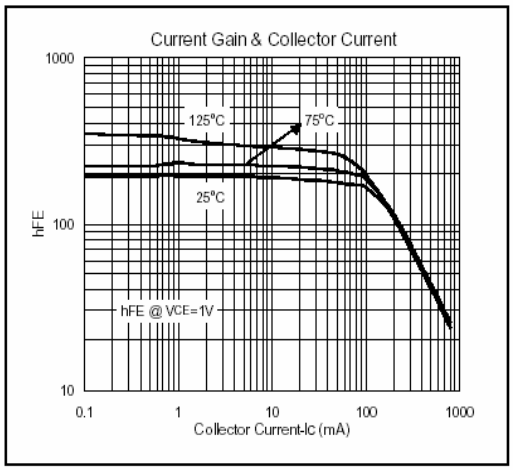
Parameter	Symbol	Ratings	Unit
Junction Temperature	Tj	+150	℃
Storage Temperature	Tstg	-55 ~ +150	℃
Collector to Base Voltage	V_{CBO}	75	V
Collector to Emitter Voltage	V_{CEO}	40	V
Emitter to Base Voltage	V_{EBO}	6	V
Collector Current	I_C	600	mA
Total Power Dissipation	P_D	625	mW

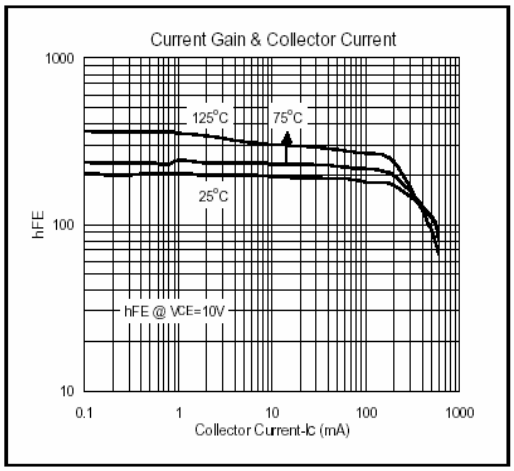
Characteristics at Ta = 25℃

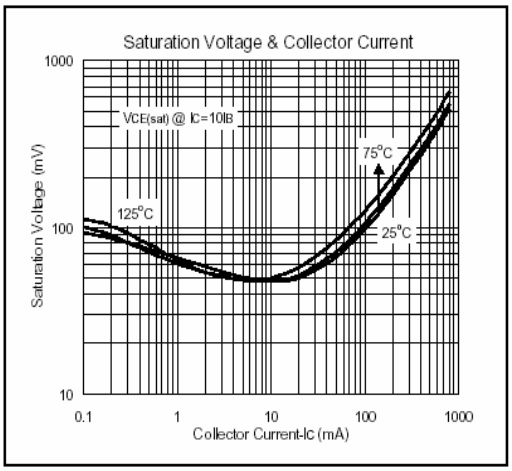
Symbol	Min.	Typ.	Max.	Unit	Test Conditions
BV_{CBO}	75	-	-	V	I_C=10uA ,I_E=0
BV_{CEO}	40	-	-	V	I_C=10mA ,I_B=0
BV_{EBO}	6	-	-	V	I_E=10uA ,I_C=0
I_{CBO}	-	-	10	nA	V_{CE}=60V, I_E = 0
I_{CEX}	-	-	10	nA	V_{CE}=60V,$V_{BE(OFF)}$=3V
I_{EBO}	-	-	50	nA	V_{EB}=3V, Ic = 0
*$V_{CE(sat)1}$	-	-	0.3	V	I_C=150mA, I_B=15mA
*$V_{CE(sat)2}$	-	-	1.0	V	I_C=500mA, I_B=50mA
*$V_{BE(sat)1}$	-	-	1.2	V	I_C=150mA, I_B=15mA
* $V_{BE(sat)2}$	-	-	2	V	I_C=500mA, I_B=50mA
*hFE1	35	-	-		V_{CE}=10V, I_C=100uA
*hFE2	50	-	-		V_{CE}=10V, I_C=1mA
*hFE3	75	-	-		V_{CE}=10V,I_C=10mA
*hFE4	100	-	300		V_{CE}=10V,I_C=150mA
*hFE5	40	-	-		V_{CE}=10V,I_C=500mA
*hFE6	50	-	-		V_{CE}=1V,I_C=150mA
fT	300	-	-	MHz	V_{CE}=20V, I_C=20mA, f=100MHz
Cob	-	-	8	pF	V_{CB}=10V, I_E = 0,f=1MHz

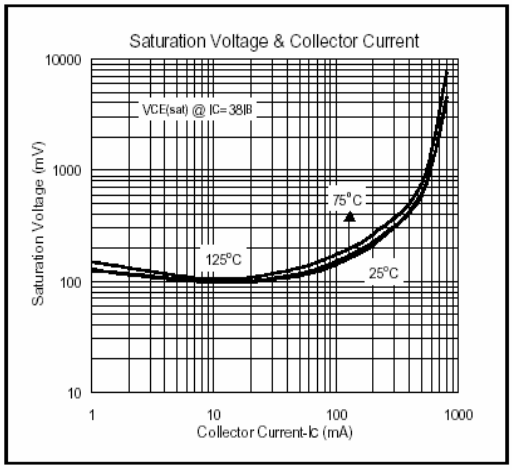
* Pulse Test: Pulse Width≦380us, Duty Cycle≦2%

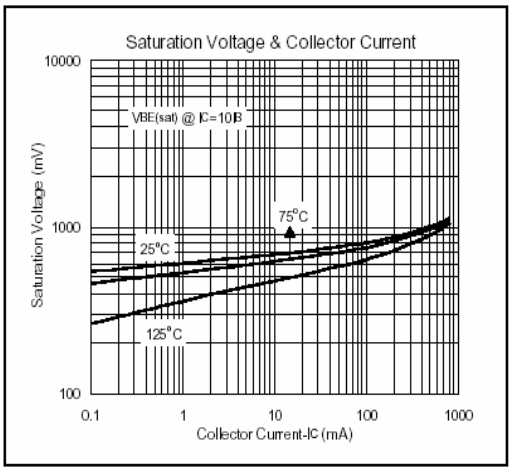
Characteristics Curve

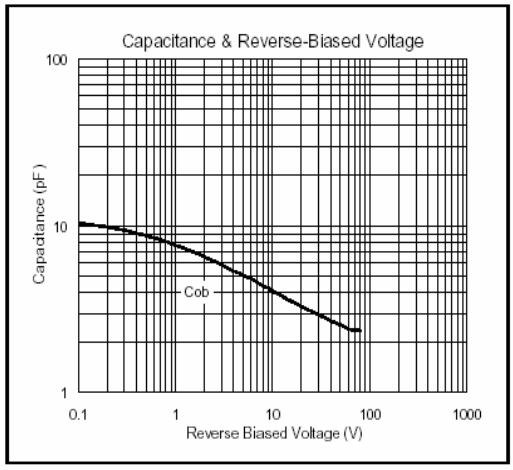


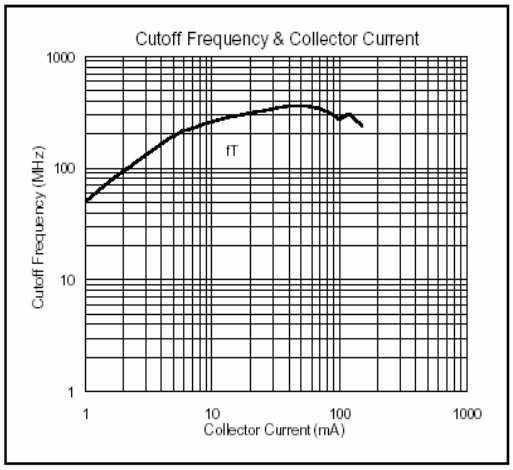


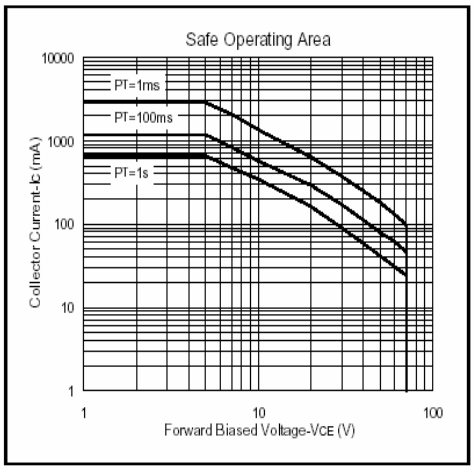


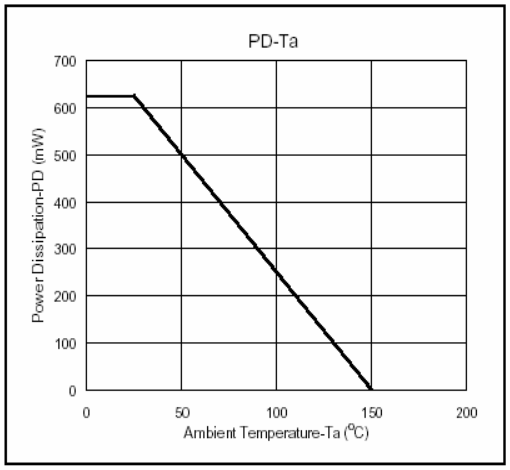












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